

DERWENT-ACC-NO: 2002-252539  
DERWENT-WEEK: 200230  
COPYRIGHT 1999 DERWENT INFORMATION LTD

TITLE: Method for forming dielectric layer with capability to resist the diffusion of copper effectively increases the capability to resist the diffusion of copper for the material with a low dielectric constant

INVENTOR: JANG, D; LIOU, B

PATENT-ASSIGNEE: UNITED MICROELECTRONICS CORP[UNMIN]

PRIORITY-DATA: 1999TW-0122132 (December 16, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 429473 A	April 11, 2001	N/A	000	H01L 021/31

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
TW 429473A	N/A	1999TW-0122132	December 16, 1999

INT-CL (IPC): H01L021/31

ABSTRACTED-PUB-NO: TW 429473A

BASIC-ABSTRACT: NOVELTY - A method for forming dielectric layer with a capability to resist the diffusion of copper comprises the steps of: first, providing a substrate and then performing a spin-on step to form a dielectric layer with a low dielectric constant on the substrate; then, sequentially performing a baking step and a curing step; and finally, performing a plasma processing step to the dielectric layer.

CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS:

METHOD FORMING DIELECTRIC LAYER CAPABLE RESIST DIFFUSION  
COPPER EFFECT INCREASE  
CAPABLE RESIST DIFFUSION COPPER MATERIAL LOW DIELECTRIC  
CONSTANT

**BEST AVAILABLE COPY**

**EV182656495**

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C12;

EPI-CODES: U11-B;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2002-075594

Non-CPI Secondary Accession Numbers: N2002-194653

---

**BEST AVAILABLE COPY**